Ronald van Langevelde

List of Publications by Year in Descending Order

37 papers	1,576 citations	17 h-index	39 g-index
39 ext. papers	1,917 ext. citations	2.8 avg, IF	3.87 L-index

#	Paper	IF	Citations
37	Parameter Extraction for the PSPHV LDMOS Transistor Model. *IEEE Journal of the Electron Devices Society*, **2020**, 8, 813-824	2.3	0
36	**2019**,		3
35	. *IEEE Transactions on Electron Devices*, **2019**, 66, 5246-5253	2.9	1
34	Experimental Demonstration and Modeling of Excess RF Noise in Sub-100-nm CMOS Technologies. *IEEE Electron Device Letters*, **2010**, 31, 884-886	4.4	9
33	RF Characterization of Schottky Diodes in 65-nm CMOS. *IEEE Transactions on Electron Devices*, **2010**, 57, 1063-1068	2.9	18
32	Surface-Potential-Based Compact Model of Bulk MOSFET **2010**, 3-40		10
31	Benchmark Tests for MOSFET Compact Models With Application to the PSP Model. *IEEE Transactions on Electron Devices*, **2009**, 56, 243-251	2.9	31
30	PSP-SOI: An advanced surface potential based compact model of partially depleted SOI MOSFETs for circuit simulations. *Solid-State Electronics*, **2009**, 53, 18-29	1.7	16
29	An ultra-low-power 868/915 MHz RF transceiver for wireless sensor network applications **2009**,		39
28	The New CMC Standard Compact MOS Model PSP: Advantages for RF Applications. *IEEE Journal of Solid-State Circuits*, **2009**, 44, 1415-1424	5.5	20
27	(Invited) The new CMC standard compact MOS model PSP: advantages for RF applications **2008**,		2
26	PSP-SOI: A Surface Potential Based Compact Model of Partially Depleted SOI MOSFETs **2007**,		12
25	PSP-Based Scalable MOS Varactor Model **2007**,		8
24	A Compact Model for Valence-Band Electron Tunneling Current in Partially Depleted SOI MOSFETs. *IEEE Transactions on Electron Devices*, **2007**, 54, 316-322	2.9	12
23	Benchmarking the PSP Compact Model for MOS Transistors **2007**,		12
22	A Unified Nonquasi-Static MOSFET Model for Large-Signal and Small-Signal Simulations. *IEEE Transactions on Electron Devices*, **2006**, 53, 2035-2043	2.9	20
21	The Physical Background of JUNCAP2. *IEEE Transactions on Electron Devices*, **2006**, 53, 2098-2107	2.9	29

20	PSP: An Advanced Surface-Potential-Based MOSFET Model for Circuit Simulation. *IEEE Transactions on Electron Devices*, **2006**, 53, 1979-1993	2.9	259
19	PSP-based compact FinFET model describing dc and RF measurements **2006**,		19
18	Compact modeling of noise in CMOS **2006**,		12
17	Analog circuits in ultra-deep-submicron CMOS. *IEEE Journal of Solid-State Circuits*, **2005**, 40, 132-143	5.5	235
16	A surface-potential-based high-voltage compact LDMOS transistor model. *IEEE Transactions on Electron Devices*, **2005**, 52, 999-1007	2.9	46
15	Generalizations of the Klaassen-Prins equation for calculating the noise of semiconductor devices. *IEEE Transactions on Electron Devices*, **2005**, 52, 2463-2472	2.9	57
14	Modeling and characterization of noise in 90-nm RF CMOS technology. *AIP Conference Proceedings*, **2005**,	0	3
13	Compact modelling of noise for RF CMOS circuit design. *IET Circuits, Devices and Systems*, **2004**, 151, 167		24
12	An advanced explicit surface potential model physically accounting for the quantization effects in deep-submicron MOSFETs. *Solid-State Electronics*, **2004**, 48, 427-435	1.7	36
11	Compact modeling of noise for RF CMOS circuit simulation **2003**,		2
10	Noise modeling for RF CMOS circuit simulation. *IEEE Transactions on Electron Devices*, **2003**, 50, 618-632	2.9	248
9	A Robust and Physically Based Compact SOI-LDMOS Model **2002**,		1
8	RF-CMOS performance trends. *IEEE Transactions on Electron Devices*, **2001**, 48, 1776-1782	2.9	204
7	Compact modelling of pocket-implanted MOSFETs **2001**,		6
6	Advanced Compact MOS Modelling **2001**,		8
5	An explicit surface-potential-based MOSFET model for circuit simulation. *Solid-State Electronics*, **2000**, 44, 409-418	1.7	103
4	RF Distortion Characterisation of Sub-Micron CMOS **2000**,		5
3	Effect of gate-field dependent mobility degradation on distortion analysis in MOSFETs. *IEEE Transactions on Electron Devices*, **1997**, 44, 2044-2052	2.9	56

2 Noise in DMOS transistors in a BICMOS-technology. *IEEE Transactions on Electron Devices*, **1996**, 43, 1243-1250 2

1 Unified non-quasi-static MOSFET model for large-signal and small-signal simulations 8